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S/N 08/757,873

PATENT

**GROUP 1100**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Umesh K. Mishra, et al.

Examiner: S. Mulpuri

Serial No.: 08/757,873

Group Art Unit: 1107

Filed: November 27, 1996

Docket: 30794.12US01

Title: UV ASSISTED GALLIUM NITRIDE GROWTH

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated June 26, 1997,  
and in response to the telephone interviews of November 5, 1997,  
please amend the application as follows:

IN THE CLAIMS

1. (Twice Amended) A method of growing a nitride layer on  
a substrate, comprising the steps of:

adding a plasma [ molecule ] gas. the gas selected from a  
group consisting of mercury, argon, neon, and xenon, to a chamber  
containing a nitrogen-bearing molecule;